Miguel Angel Gonzalez Rebollo

List of Publications by Year
in descending order

47 papers	366 citations	933447 10 h-index	888059 17 g-index
50 all docs	50 docs citations	50 times ranked	258 citing authors

#	Article	IF	Citations
1	Low-Cost Electronics for Online I-V Tracing at Photovoltaic Module Level: Development of Two Strategies and Comparison between Them. Electronics (Switzerland), 2021, 10, 671.	3.1	12
2	Daylight luminescence system for silicon solar panels based on a bias switching method. Energy Science and Engineering, 2020, 8, 3839-3853.	4.0	17
3	Photoluminescence Imaging and LBIC Characterization of Defects in mc-Si Solar Cells. Journal of Electronic Materials, 2018, 47, 5077-5082.	2.2	1
4	Open-source sensors system for doing simple physics experiments. Papers in Physics, 2018, 10, .	0.2	1
5	Smartphones on the air track. Examples and difficulties. Papers in Physics, 2018, 10, .	0.2	1
6	Smartphones as experimental tools to measure acoustical and mechanical properties of vibrating rods. European Journal of Physics, 2016, 37, 045701.	0.6	24
7	Defect recognition by means of light and electron probe techniques for the characterization of mc-Si wafers and solar cells. Superlattices and Microstructures, 2016, 99, 45-53.	3.1	3
8	Doing physics experiments and learning with smartphones. , 2015, , .		6
9	Teaching and Learning Physics with Smartphones. Journal of Cases on Information Technology, 2015, 17, 31-50.	0.7	41
10	Analysis of the reduction of tensile stress by post-growth annealing methods in multicrystalline silicon wafers produced by the RST process. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 1640-1643.	0.8	1
11	Residual Strain and Electrical Activity of Defects in Multicrystalline Silicon Solar Cells. Acta Physica Polonica A, 2014, 125, 1013-1016.	0.5	3
12	Raman Study of Multicrystalline Silicon Wafers Produced by the RST Process. Acta Physica Polonica A, 2014, 125, 1006-1009.	0.5	0
13	Analysis of the Residuals in Grave Goods From the Vaccaea Era at the Necropolis of â€œLas Ruedasâ€•in Pintia. Spectroscopy Letters, 2012, 45, 141-145.	1.0	2
14	Study of the crystal features of mc-Si PV cells by laser beam induced current (LBIC). Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1330-1333.	0.8	7
15	A Spectrum Image Cathodoluminescence Study of Dislocations in Si-Doped Liquid-Encapsulated Czochralski GaAs Crystals. Journal of Electronic Materials, 2010, 39, 781-786.	2.2	2
16	LBIC and Reflectance Mapping of Multicrystalline Si Solar Cells. Journal of Electronic Materials, 2010, 39, 663-670.	2.2	26
17	Light Beam Induced Current Mapping of mc-Si Solar Cells: Influence of Grain Boundaries and Intragrain Defects. Materials Research Society Symposia Proceedings, 2010, 1268, 1.	0.1	2
18	MotionLab. , 2010, , .		1

#	ARTICLE	IF	CITATIONS
19	Spectral image cathodoluminescence, photoluminescence and Raman study of GaAs layers grown on Si substrates. Superlattices and Microstructures, 2009, 45, 214-221.	3.1	0
20	Hydrogen-free SiCN Films Obtained by Electron Cyclotron Resonance Plasma. Journal of the Electrochemical Society, 2007, 154, H325.	2.9	1
21	Blue-cathodoluminescent layers synthesis by high-dose N+, C+ and B+ SiO2 implantation. Journal of Luminescence, 2006, 117, 95-100.	3.1	6
22	InP surface properties under ICP plasma etching using mixtures of chlorides and hydrides. Materials Science in Semiconductor Processing, 2006, 9, 225-229.	4.0	8
23	Optical and structural characterization of GaN/AlN quantum dots grown on Si(111). Journal of Physics Condensed Matter, 2002, 14, 13329-13336.	1.8	9
24	Optical and structural characterization of LP MOVPE grown lattice matched InGaP/GaAs heterostructures. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 91-92, 123-127.	3.5	2
25	Selective doping of conformal GaAs layers grown by hydride vapour phase epitaxy on Si substrates studied by spatially resolved optical techniques. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 80, 197-201.	3.5	1
26	MicroRaman and phase stepping microscopy analysis of growth defects in GaAs/GaAs epilayers. Materials Science and Technology, 1998, 14, 1286-1290.	1.6	1
27	Temperature dependence of the photoquenching of EL2 in semi-insulating GaAs. Applied Physics Letters, 1997, 70, 3131-3133.	3.3	3
28	Homogeneity of Fe-Doped InP Wafers Using Optical Microprobes. Materials Science Forum, 1997, 258-263, 825-830.	0.3	1
29	Homogeneity of thermally annealed Fe-doped InP wafers. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1997, 44, 233-237.	3.5	7
30	Metastable transformation of EL2 in semiâ€insulating GaAs: The role of the actuator level and the photoionization of EL2. Applied Physics Letters, 1996, 68, 2959-2961.	3.3	12
31	Photocurrent contrast in semi-insulating Fe-doped InP. Semiconductor Science and Technology, 1996, 11, 941-946.	2.0	9
32	MicroRaman analysis of twin lamellae in undoped LEC InP. Journal of Materials Science: Materials in Electronics, 1994, 5, 315-320.	2.2	1
33	Photocurrent study of Fe-doped semi-insulating InP. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1994, 28, 111-114.	3.5	3
34	Characterization of the homogeneity of semi-insulating InP by the spatially resolved photocurrent. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1993, 20, 105-108.	3.5	5
35	A comparison of the thermal and near bandâ€gap lightâ€induced recoveries ofEL2 from its metastable state in semiinsulating GaAs. Journal of Applied Physics, 1993, 73, 5004-5008.	2.5	9
36	Low-temperature spatially resolved photoconductivity in semi-insulating GaAs. Semiconductor Science and Technology, 1992, 7, A202-A206.	2.0	8

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37	Study of the Inhomogeneities in Semiinsulating GaAs and InP by Spatially Resolved Photoconductivity. Materials Research Society Symposia Proceedings, 1992, 261, 241.	0.1	0
38	Raman microprobe analysis of GaAs wafers. Journal of Crystal Growth, 1990, 103, 54-60.	1.5	8
39	0.8 eV excitation of the quenched EL2* level in semiâ€insulating GaAs. Journal of Applied Physics, 1989, 66, 2221-2222.	2.5	3
40	Optical recovery of the 1â€“1.3 eV photocurrent by 1.45eV photons in semiinsulating GaAs. Solid State Communications, 1989, 72, 781-783.	1.9	4
41	Optical Quenching of the Extrinsic Light Induced Enhanced Photocurrent in Semi-Insulating GaAs. Japanese Journal of Applied Physics, 1988, 27, 1841-1844.	1.5	8
42	Photo-Hall study of the optically enhanced photocurrent in semi-insulating LEC GaAs. Solid State Communications, 1987, 63, 937-940.	1.9	12
43	Optically enhanced defect reactions in semiâ€insulating bulk GaAs. Journal of Applied Physics, 1985, 57, 1152-1160.	2.5	38
44	Optical Photogenerated Traps in Semi-Insulating GaAs Bulk Material. Physica Scripta, 1984, 30, 198-200.	2.5	7
45	Thermal quenching of the 1â€“1.35 eV extrinsic photoconductivity in semi-insulating GaAs (Cr, O). Solid State Communications, 1984, 49, 917-920.	1.9	15
46	A study on the photoconductivity of a set of horizontal Bridgman semi-insulating GaAs ingots. Journal of Materials Science, 1984, 19, 1207-1219.	3.7	16
47	Combined EL and LBIC Study of the Electrical Activity of Defects in Solar Cells Based on Innovative Wafers Grown by Casting Methods. Materials Science Forum, 0, 725, 137-140.	0.3	0